

Title (en)  
METHOD FOR PRODUCING RESIST SUBSTRATES

Title (de)  
VERFAHREN ZUR HERSTELLUNG EINES RESISTSUBSTRATS

Title (fr)  
PROCEDE DE REALISATION D'UN SUBSTRAT DE RESERVE

Publication  
**EP 1599764 A2 20051130 (DE)**

Application  
**EP 04713886 A 20040224**

Priority

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Abstract (en)  
[origin: WO2004077161A2] The invention relates to a method for producing a substrate provided with a resist layer in the form of a relief structure comprising a diffraction structure. Said resist layer interacts with at least areas provided with a conductive layer which diffuses primary electrons and/or produces secondary electrons when the resist layer is exposed to an electron beam effect. For the inventive method, the material of the resist and conductive layers and exposition parameters are co-ordinated therebetween in such a way that the resist layer is also exposed outside the area exposed to the electron beam in such a way that the lateral parts of the relief structure hold an inclined shape.

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**G03F 7/09**; H01J 37/317; G03F 7/00; G03F 7/20

IPC 8 full level  
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Citation (search report)  
See references of WO 2004077161A2

Citation (examination)  
DATABASE INSPEC [online] THE INSTITUTION OF ELECTRICAL ENGINEERS, STEVENAGE, GB; 1995, WELLS G M ET AL: "X-ray mask fabrication process", Database accession no. 5147491 & PHOTOMASK AND X-RAY MASK TECHNOLOGY II 20-21 APRIL 1995 KAWASAKI CITY, JAPAN, vol. 2512, PROCEEDINGS OF THE SPIE - THE INTERNATIONAL SOCIETY FOR OPTICAL ENGINEERING SPIE-INT. SOC. OPT. ENG. USA, pages 167 - 171, ISSN: 0277-786X

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